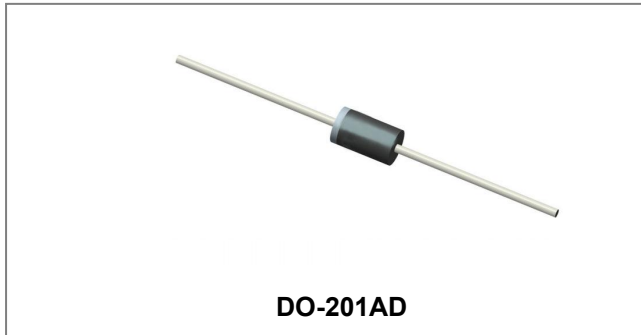


SF41G-SF48G SUPER FAST RECTIFIER



Features

- Super fast switching for high efficiency
- Low leakage current
- High forward surge capability
- Solder dip 260 ° C, 40 s
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Mechanical Data

- Case: JEDEC DO-201AD molded plastic body
- Terminals: Plated axial leads, solderable per MIL-STD-750, Method 2026
- Polarity: Color band denotes cathode end
- Mounting Position: Any
- Weight: 1.02 gram

Maximum Ratings and Electrical Characteristics @ $T_A=25^{\circ}\text{C}$ unless otherwise specified

Characteristic	Symbol	SF41G	SF42G	SF43G	SF44G	SF45G	SF46G	SF48G	Units
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	150	200	300	400	600	V
Maximum RMS voltage	V_{RMS}	35	70	105	140	210	280	420	V
Maximum DC blocking voltage	V_{DC}	50	100	150	200	300	400	600	V
Maximum average forward rectified current 0.375"(9.5mm) lead length at $T_A=55^{\circ}\text{C}$	$I_{(AV)}$	4.0							A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	150.0							A
Maximum instantaneous forward voltage at 4.0A	V_F	0.95			1.25		1.7		V
Maximum DC reverse current $T_A=25^{\circ}\text{C}$ at rated DC blocking voltage $T_A=100^{\circ}\text{C}$	I_R				5.0		50.0		μA
Maximum Reverse Recovery Time (Note 1)	T_{rr}	35							ns
Typical Junction Capacitance (Note 2)	C_J	100.0			50.0				pF
Typical Thermal Resistance (Note 3)	$R_{\theta JA}$	30.0							$^{\circ}\text{C}/\text{W}$
Junction Temperature	T_J	-65 to +150							$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-65 to +150							$^{\circ}\text{C}$

Note: 1. Reverse recovery condition $I_F=0.5\text{A}$, $I_R=1.0\text{A}$. $I_{rr}=0.25\text{A}$

2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

3. Thermal resistance from junction to ambient at 0.375"(9.5mm) lead length, P.C.B mounted.

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Ratings and Characteristics Curves

FIG. 1- FORWARD CURRENT DERATING CURVE

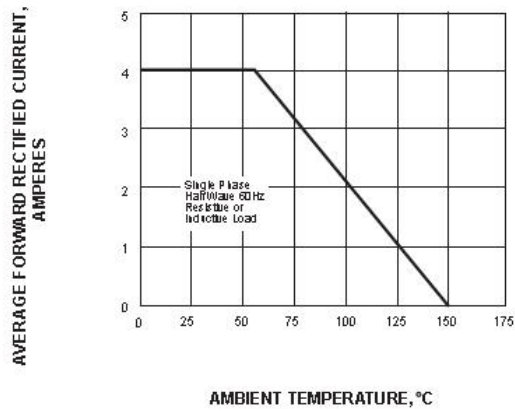


FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

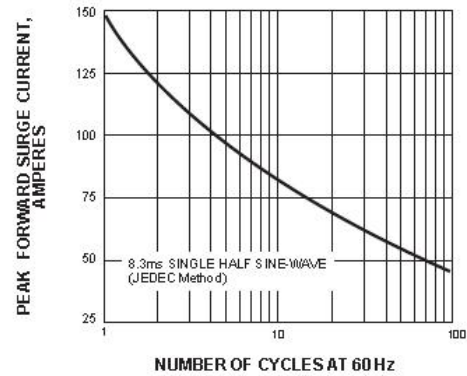


FIG. 3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

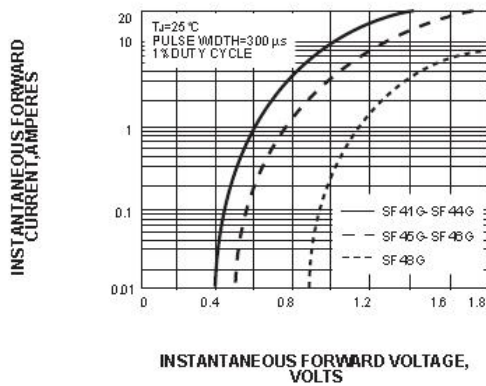
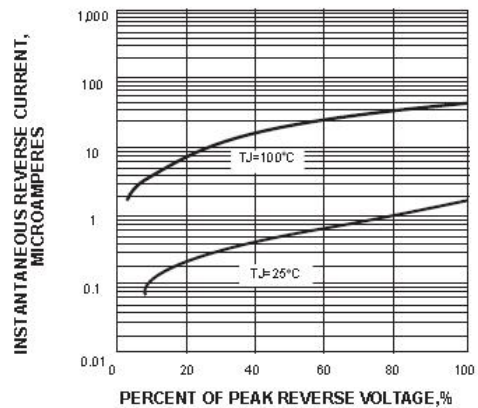
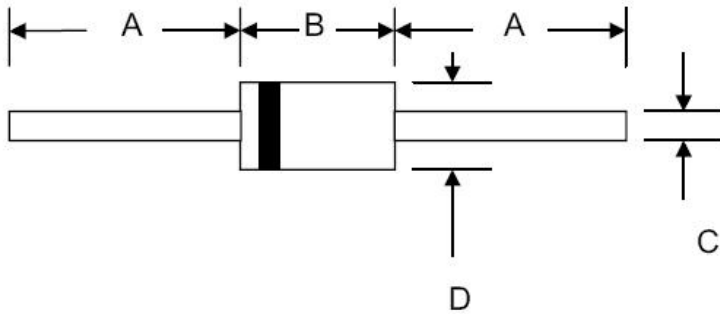


FIG. 4-TYPICAL REVERSE CHARACTERISTICS



Mechanical Dimensions DO-201AD



SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	25.4	-	1.000	-
B	8.50	9.50	0.335	0.374
C	1.2	1.3	0.048	0.052
D	5.0	5.6	0.197	0.220

Ordering Information

Device	Package	Shipping
SF41G THRU SF48G	DO-201AD (Pb-Free)	1250pcs / tape

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

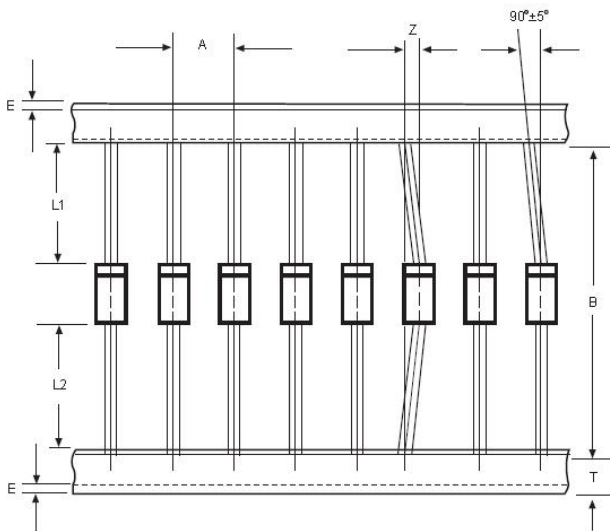
Marking Diagram



Where XXXXX is YYWWL

SF41G = Part Name
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Carrier Tape Specification DO-201AD



SYMBOL	Millimeters	
	Min.	Max.
A	9.50	10.50
B	50.9	53.9
Z	-	1.20
T	5.60	6.40
E	-	0.80
IL1-L2I	-	1.0

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